

AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended): A method for manufacturing a semiconductor laser device, comprising the steps of:

forming electrode patterns arranged in a plurality of rows extending in a first direction on an upper surface of a semiconductor wafer having at least a light emission layer, the electrode patterns having opposed two edges extending in the first direction;

cutting the resultant semiconductor wafer for predetermined width to yield a plurality of semiconductor bars; and

sectioning the semiconductor bars in desired sizes to form semiconductor laser devices each having a pair of cleavage surfaces, the surfaces being parallel to a second direction and distant from each other by a resonator length,

wherein the formed electrode patterns are continuous with each other in the first direction, each electrode pattern including a series of markers having a periodical pattern which is continuous one marker to the next in the first direction, the markers being formed ~~at~~on one or both of the edges of the electrode patterns, and a minimum unit of the periodical pattern has an overall length in the first direction equal to L/n and not greater than the resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, the second direction being perpendicular to the first direction and each laser device being cut or sectioned to have a length which is an integral multiple of the length of a marker.

Claims 2-4 (cancelled)

Claim 5 (currently amended): A semiconductor laser device, comprising:

a semiconductor layer portion including at least a light emission layer and a pair of cleavage surfaces the surfaces being parallel and distant from each other by a resonator length; and

an electrode pattern piece formed on an upper surface of the semiconductor layer portion, the electrode pattern piece having opposed two first edges extending in a first direction and opposed two second edges extending in a second direction along the pair of cleavage surfaces,

wherein the two second edges come in contact with the pair of cleavage surfaces, each electrode pattern piece including a series of markers having a periodical pattern formed ~~at~~on one or both of the first edges, a minimum unit of the periodical pattern having an overall length in the resonator-length direction equal to L/n and not greater than a resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, wherein the markers can be used to form laser chips of different resonator lengths.

Claims 6-9 (cancelled)

Claim 10 (currently amended): The device of claim 5, wherein the marker is set so that the ratio of its overall length in the resonator-length direction to its maximum length in the laser chip-width direction is 1:5 to 5:1.

Claim 11 (previously presented): The method of claim 1, wherein the semiconductor wafer is cut in predetermined widths to yield a plurality of semiconductor bars extending in the resonator-length direction, and the plurality of semiconductor bars are cut in predetermined resonator lengths.

Claim 12 (previously presented): The method of claim 11, wherein one of the semiconductor bars is cut in different resonator lengths to yield a plurality of different semiconductor laser devices.

Claim 13 (previously presented): The method of claim 11, wherein one of the semiconductor bars is cut in integral multiple lengths of the overall length of the marker.

Claim 14 (previously presented): The device of claim 5, wherein the series of markers are shaped like teeth of a saw.

Claim 15 (previously presented): The device of claim 5, wherein one of the markers is formed in a shape of right triangle, equilateral triangle, isosceles triangle, semicircle or semiellipse.